

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

The 2SK2982 is N-channel MOS Field Effect Transistor designed for high current switching applications.

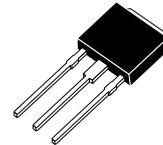
FEATURES

- Low on-resistance
 $R_{DS(on)1} = 12.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)2} = 16.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)3} = 19.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.0 \text{ V, } I_D = 15 \text{ A)}$
- Low C_{iss} : $C_{iss} = 2290 \text{ pF TYP.}$
- Built-in gate protection diode

ORDERING INFORMATION

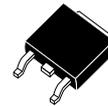
PART NUMBER	PACKAGE
2SK2982	TO-251
2SK2982-Z	TO-252

(TO-251)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	30	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 30	A
Drain Current (Pulse) ^{Note}	$I_{D(pulse)}$	± 120	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.0	W
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_T	30	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

(TO-252)



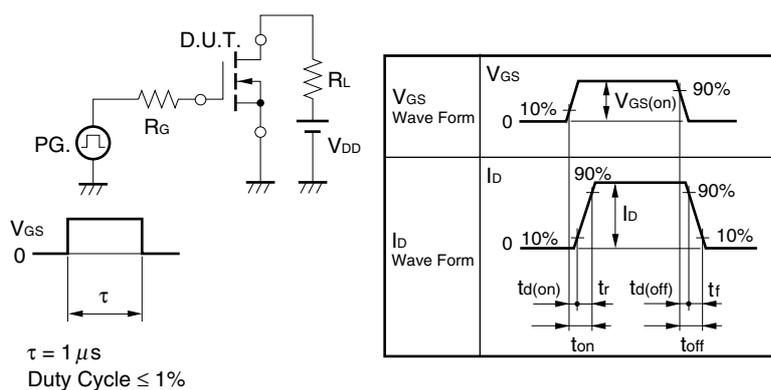
Note $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

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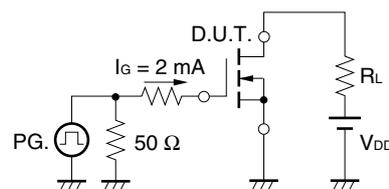
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 15 A		9.8	12.5	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 15 A		13.2	16.5	mΩ
	R _{DS(on)3}	V _{GS} = 4.0 V, I _D = 15 A		15.0	19.0	mΩ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0	1.5	2.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 15 A	13	27		S
Drain Leakage Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 10 V		2290		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		940		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		440		pF
Turn-on Delay Time	T _{d(on)}	I _D = 15 A		40		ns
Rise Time	t _r	V _{GS(on)} = 10 V		427		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = 15 V		174		ns
Fall Time	T _f	R _G = 10 Ω		226		ns
Total Gate Charge	Q _G	I _D = 30 A		53		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 24 V		6.3		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = 10 V		16		nC
Body Diode forward Voltage	V _{F(S-D)}	I _F = 30 A, V _{GS} = 0 V		0.8		V
Reverse Recovery Time	T _{rr}	I _F = 30A, V _{GS} = 0 V		49		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs		50		nC

TEST CIRCUIT 1 SWITCHING TIME

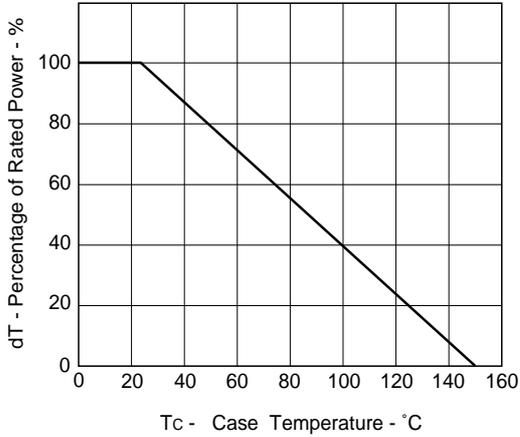


TEST CIRCUIT 2 GATE CHARGE

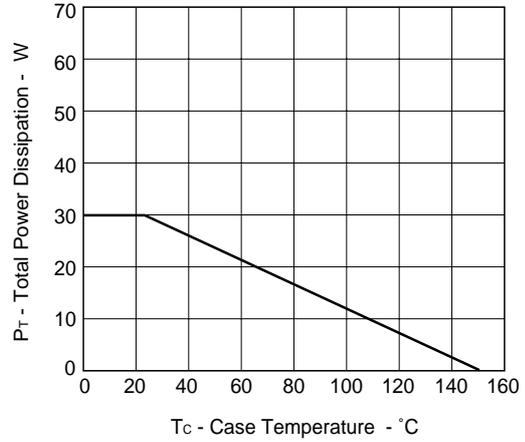


TYPICAL CHARACTERISTICS (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

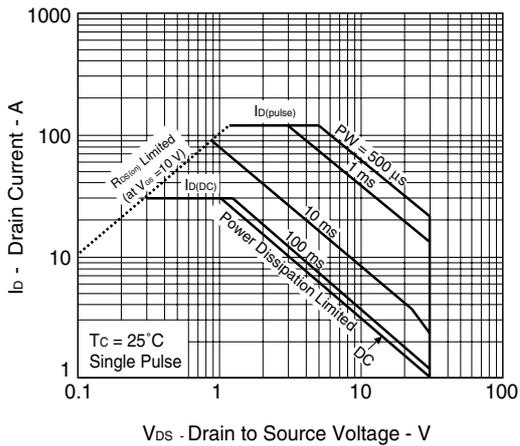


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

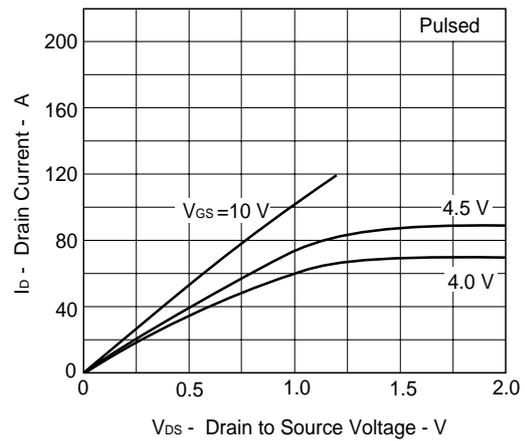


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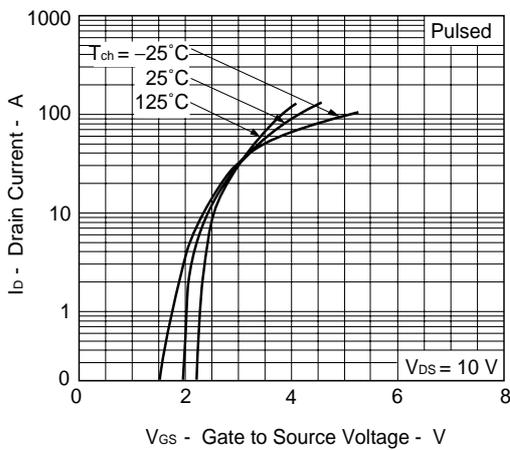
FORWARD BIAS SAFE OPERATING AREA



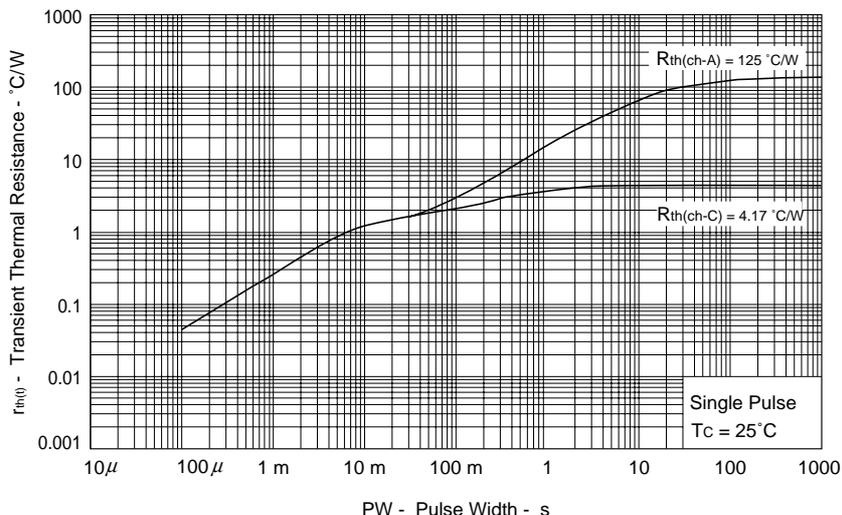
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



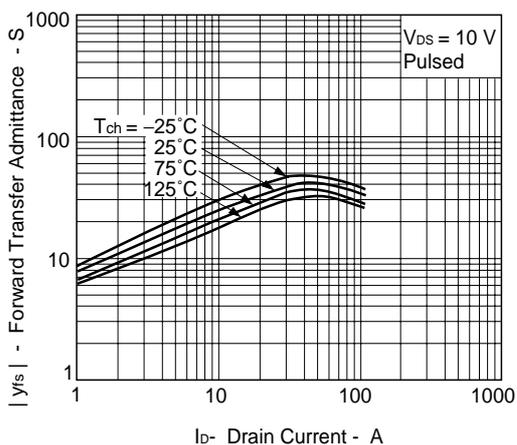
FORWARD TRANSFER CHARACTERISTICS



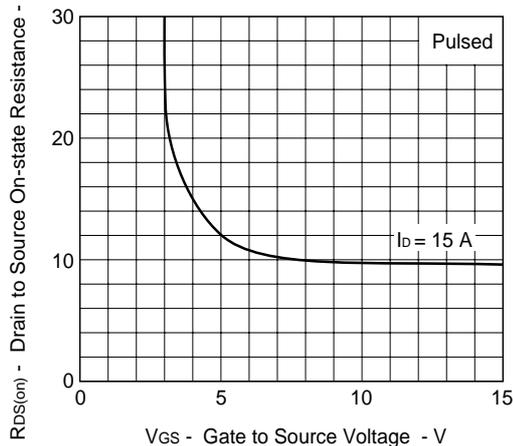
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



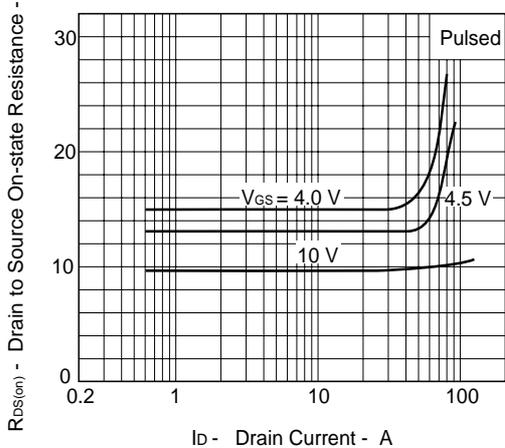
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



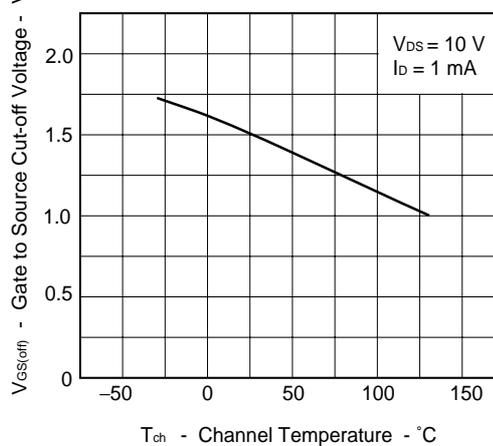
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



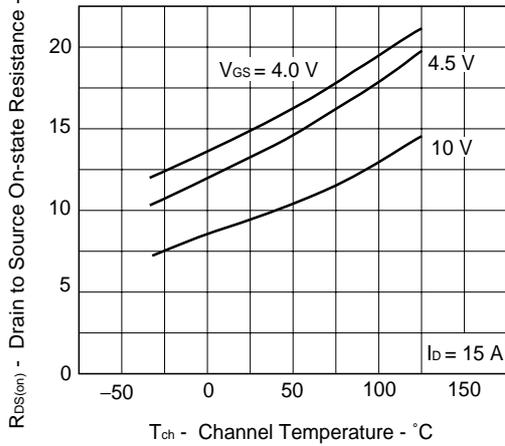
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



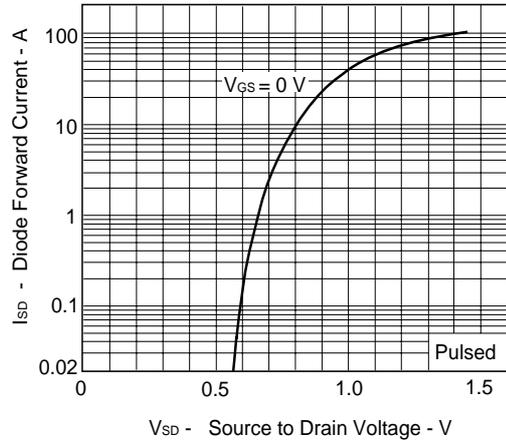
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



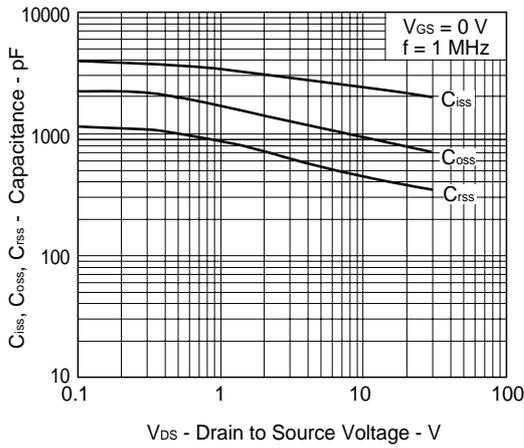
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



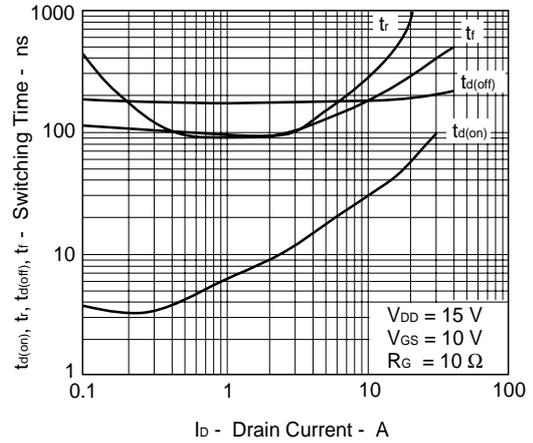
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



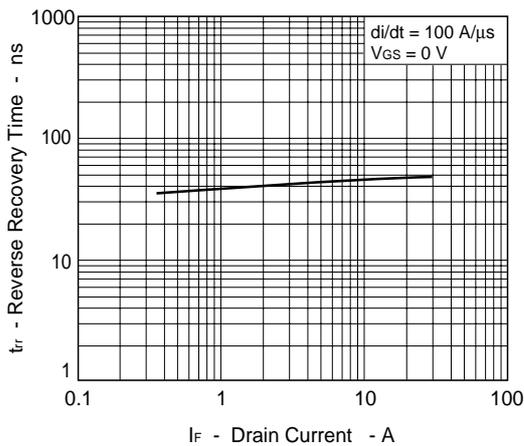
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



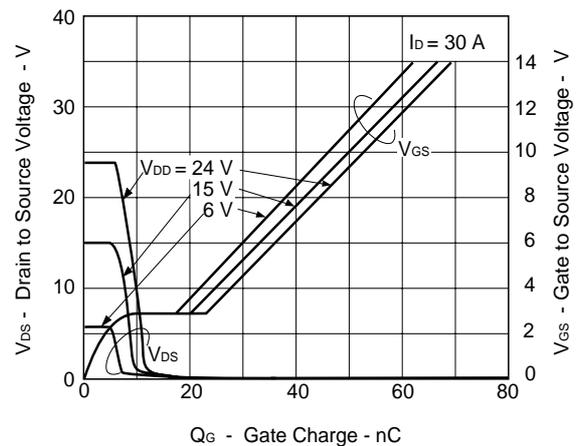
SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DRAIN CURRENT

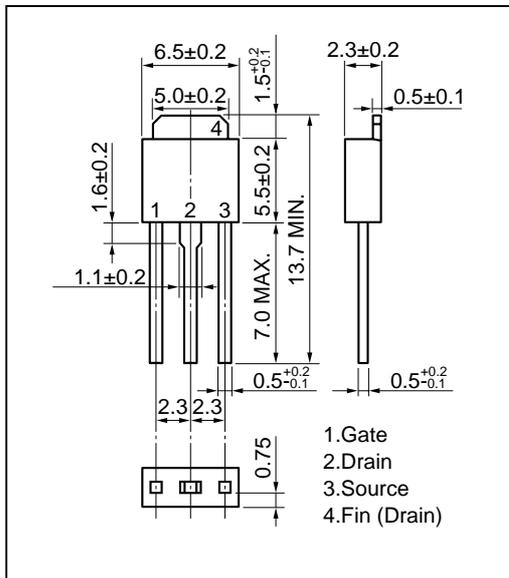


DYNAMIC INPUT/OUTPUT CHARACTERISTICS

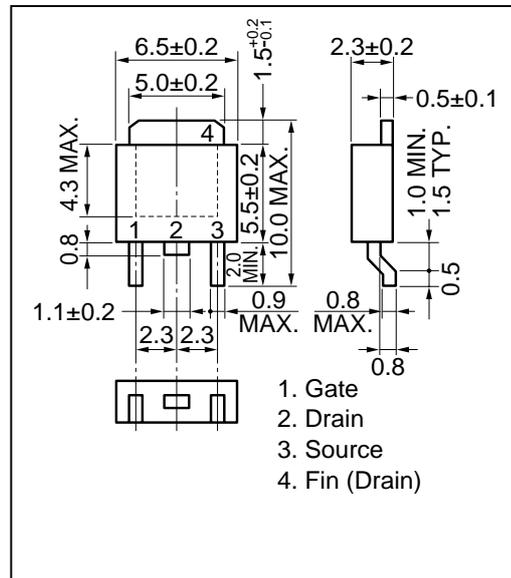


PACKAGE DRAWINGS (Unit: mm)

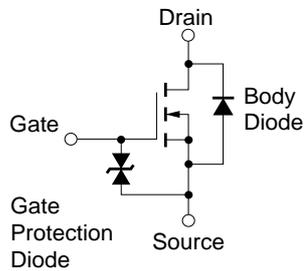
TO-251(MP-3)



TO-252(MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

[MEMO]

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